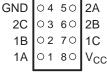
FEATURES

- Available in the Texas Instruments
 NanoFree™ Package
- Operates at 0.8 V to 2.7 V
- Sub-1-V Operable
- Max t_{pd} of 0.5 ns at 1.8 V
- Low Power Consumption, 10 μA at 2.7 V
- High On-Off Output Voltage Ratio
- · High Degree of Linearity
- Latch-Up Performance Exceeds 100 mA Per JESD 78, Class II
- ESD Performance Tested Per JESD 22
 - 2000-V Human-Body Model (A114-B, Class II)
 - 200-V Machine Model (A115-A)
 - 1000-V Charged-Device Model (C101)

1A 1 8 V_{CC} 1B 2 7 1C 2C 3 6 2B GND 4 5 2A





DESCRIPTION/ORDERING INFORMATION

This dual analog switch is operational at 0.8-V to 2.7-V V_{CC} , but is designed specifically for 1.1-V to 2.7-V V_{CC} operation.

The SN74AUC2G66 can handle both analog and digital signals. It permits signals with amplitudes of up to 2.7-V (peak) to be transmitted in either direction.

NanoFree™ package technology is a major breakthrough in IC packaging concepts, using the die as the package.

Applications include signal gating, chopping, modulation or demodulation (modem), and signal multiplexing for analog-to-digital and digital-to-analog conversion systems.

ORDERING INFORMATION

T _A	PACKAGE ⁽¹⁾		ORDERABLE PART NUMBER	TOP-SIDE MARKING ⁽²⁾
	NanoFree™ – WCSP (DSBGA) 0.23-mm Large Bump – YZP (Pb-free)	Reel of 3000	SN74AUC2G66YZPR	U6_
-40°C to 85°C	SSOP - DCT	Reel of 3000	SN74AUC2G66DCTR	U66
	VSSOP - DCU	Reel of 3000	SN74AUC2G66DCUR	U66_

(1) Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

(2) DCT: The actual top-side marking has three additional characters that designate the year, month, and assembly/test site. DCU: The actual top-side marking has one additional character that designates the assembly/test site. YZP: The actual top-side marking has three preceding characters to denote year, month, and sequence code, and one following character to designate the assembly/test site. Pin 1 identifier indicates solder-bump composition (1 = SnPb, • = Pb-free).

FUNCTION TABLE

CONTROL INPUT (C)	SWITCH
L	OFF
Н	ON

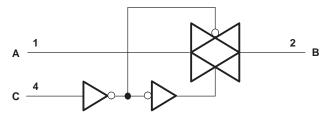
ΔĀ

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

NanoFree is a trademark of Texas Instruments.



LOGIC DIAGRAM (POSITIVE LOGIC)



Absolute Maximum Ratings(1)

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V_{CC}	Supply voltage range ⁽²⁾		-0.5	3.6	V
V_{I}	Input voltage range (2)(3)			3.6	V
V _{I/O}	Switch I/O voltage range (2)(3)	Switch I/O voltage range (2)(3)		V _{CC} + 0.5	V
I _{IK}	Control input clamp current	V ₁ < 0		-50	mA
I _{IOK}	I/O port diode current	$V_{I/O}$ < 0 or $V_{I/O}$ > V_{CC}		±50	mA
I _T	On-state switch current	$V_{I/O} = 0 \text{ to } V_{CC}$		±50	mA
	Continuous current through V _{CC} or GND			±100	mA
		DCT package		220	
θ_{JA}	Package thermal impedance (4)	DCU package		227	°C/W
		YZP package		102	
T _{stg}	Storage temperature range	·	- 65	150	°C

⁽¹⁾ Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

⁽²⁾ All voltages are with respect to ground unless otherwise specified.

 ⁽³⁾ The input negative-voltage and output voltage ratings may be exceeded if the input and output current ratings are observed.
 (4) The package thermal impedance is calculated in accordance with JESD 51-7.

Recommended Operating Conditions⁽¹⁾

			MIN	MAX	UNIT
V_{CC}	Supply voltage		0.8	2.7	V
		V _{CC} = 0.8 V	V _{CC}		
V_{IH}	High-level input voltage	V _{CC} = 1.1 V to 1.95 V	0.65 × V _{CC}		V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}$	1.7		
		V _{CC} = 0.8 V		0	
V_{IL}	Low-level input voltage	V _{CC} = 1.1 V to 1.95 V		$0.35 \times V_{CC}$	V
	L Low-level input voltage	V _{CC} = 2.3 V to 2.7 V		0.7	
V _{I/O}	I/O port voltage		0	V _{CC}	V
V_{I}	Control input voltage		0	3.6	V
		$V_{CC} = 0.8 \text{ V to } 1.65 \text{ V}^{(2)}$		20	
Δt/Δν	Input transition rise or fall rate	$V_{CC} = 1.65 \text{ V to } 2.3 \text{ V}^{(3)}$		20	ns/V
		$V_{CC} = 2.3 \text{ V to } 2.7 \text{ V}^{(3)}$		20	
T _A	Operating free-air temperature		-40	85	°C

All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.
 The data was taken at C_L = 15 pF, R_L = 2 kΩ (see Figure 1).
 The data was taken at C_L = 30 pF, R_L = 500 Ω (see Figure 1).

Electrical Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

	PARAMETER	TEST CONDITION	NS	V _{cc}	MIN TYP(1)	MAX	UNIT
		$V_I = V_{CC}$ or GND,	$I_S = 4 \text{ mA}$	1.1 V	17	40	
r _{on}	On-state switch resistance	$V_C = V_{IH}$	IS = 4 IIIA	1.65 V	7	20	Ω
		(see Figure 1 and Figure 2)	$I_S = 8 \text{ mA}$	2.3 V	4	15	
		$V_I = V_{CC}$ to GND,	$I_S = 4 \text{ mA}$	1.1 V	131	180	Ω
r _{on(p)}	Peak on resistance	$V_C = V_{IH}$	IS - 4 IIIA	1.65 V	32	80	
		(see Figure 1 and Figure 2)	$I_S = 8 \text{ mA}$	2.3 V	15	20	
	Difference of	$V_{I} = V_{CC}$ to GND,	1 4 50 1	1.1 V		3	
Δr_{on}	on-state resistance between switches	$V_C = V_{IH}$	$I_S = 4 \text{ mA}$	1.65 V		1	Ω
		(see Figure 1 and Figure 2)	$I_S = 8 \text{ mA}$	2.3 V		1	
		$V_I = V_{CC}$ and $V_O = GND$, or				±1	
I _{S(off)}	Off-state switch leakage current	$V_I = GND$ and $V_O = V_{CC}$, $V_C = V_{IL}$ (see Figure 3)		2.7 V		±0.1 ⁽²⁾	μА
	On-state switch leakage current	$V_I = V_{CC}$ or GND, $V_C = V_{IH}$, V_C	/ _O = Open	2.7 V		±1	μΑ
I _{S(on)}	On-state switch leakage current	(see Figure 4)		2.7 V		±0.1 ⁽²⁾	μΑ
I _I	Control input current	$V_I = V_{CC}$ or GND		0 to 2.7 V		±5	μΑ
I _{CC}	Supply current	$V_I = V_{CC}$ or GND,	I _O = 0	0.8 V to 2.7 V		10	μΑ
C _{ic}	Control input capacitance			2.5 V	2.5		pF
C _{io(off)}	Switch input/output capacitance			2.5 V	3		pF
C _{io(on)}	Switch input/output capacitance			2.5 V	7		pF

⁽¹⁾ t_a = 25°C (2) The data was taken at C_L = 15 pF, R_L = 2 k Ω (see Figure 1).



Switching Characteristics

over recommended operating free-air temperature range, $C_L = 15 \text{ pF}$ (unless otherwise noted) (see Figure 5)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 0.8 V	V _{CC} = ± 0.7		V _{CC} = 0.1			c = 1.8 0.15 \		V _{CC} = 2 ± 0.2		UNIT
	(INFO1)	(0011-01)	TYP	MIN	MAX	MIN	MAX	MIN	TYP	MAX	MIN	MAX	
t _{pd} ⁽¹⁾	A or B	B or A	1		0.6		0.5			0.5		0.4	ns
t _{en}	С	A or B	5	0.5	3	0.5	2.1	0.5	0.9	1.6	0.5	1.4	ns
t _{dis}	С	A or B	5.3	0.5	4	0.5	3	0.5	2.6	3.3	0.5	2.7	ns

⁽¹⁾ The propagation delay is the calculated RC time constant of the typical on-state resistance of the switch and the specified load capacitance when driven by an ideal voltage source (zero output impedance).

Switching Characteristics

over recommended operating free-air temperature range, $C_L = 30 \text{ pF}$ (unless otherwise noted) (see Figure 5)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = 1.8 V ± 0.15 V			V _{CC} = 2.5 V ± 0.2 V		UNIT
	(INPUT)	(OUTPUT)	MIN	TYP	MAX	MIN	MAX	
t _{pd} ⁽¹⁾	A or B	B or A			0.7		0.7	ns
t _{en}	С	A or B	0.5	1.6	2.7	0.5	2.3	ns
t _{dis}	С	A or B	0.5	2.7	3.4	0.5	2	ns

⁽¹⁾ The propagation delay is the calculated RC time constant of the typical on-state resistance of the switch and the specified load capacitance when driven by an ideal voltage source (zero output impedance).

Analog Switch Characteristics

 $T_A = 25^{\circ}C$

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	V _{cc}	TYP	UNIT
				0.8 V	101	
			$C_L = 50 \text{ pF}, R_L = 600 \Omega,$	1.1 V	150	
			f _{in} = sine wave	1.4 V	175	
			(see Figure 6)	1.65 V	250	
Frequency response				2.3 V	400	
(switch ON)	A or B	B or A		0.8 V	450	MHz
			$C_L = 5 \text{ pF}, R_L = 50 \Omega,$	1.1 V	>500	
			f _{in} = sine wave	1.4 V	>500	
			(see Figure 6)	1.65 V	>500	
				2.3 V	>500	
				0.8 V	-60	dB
			$C_L = 50 \text{ pF}, R_L = 600 \Omega,$	1.1 V	-60	
			f _{in} = 1 MHz (sine wave)	1.4 V	-60	
			(see Figure 7)	1.65 V	-60	
Crosstalk	A == D	D A		2.3 V	-60	
(between switches)	A or B	B or A		0.8 V	-65	
			$C_L = 5 \text{ pF}, R_L = 50 \Omega,$	1.1 V	-65	
			f _{in} = 1 MHz (sine wave)	1.4 V	-65	
			(see Figure 7)	1.65 V	-65	
				2.3 V	-65	

SCES507A-NOVEMBER 2003-REVISED JANUARY 2007

Analog Switch Characteristics (continued)

T_A = 25°C

PARAMETER	FROM (INPUT)	TO (OUTPUT)	TEST CONDITIONS	V _{cc}	TYP	UNIT
				0.8 V	9	
Crosstalk			$C_L = 50 \text{ pF}, R_L = 600 \Omega,$	1.1 V	14	mV
(control input to signal	С	A or B	f _{in} = 1 MHz (square wave)	1.4 V	15	
output)			(see Figure 8)	1.65 V	16	
				2.3 V	20	
				0.8 V	-50	
Feedthrough attenuation (switch OFF)			$C_L = 50 \text{ pF}, R_L = 600 \Omega,$	1.1 V	– 50	
	A or B	B or A	f _{in} = 1 MHz (sine wave)	1.4 V	– 50	
			(see Figure 9)	1.65 V	-50	dB
				2.3 V	-50	
	A OF B			0.8 V	-60	
			$C_L = 5 \text{ pF}, R_L = 50 \Omega,$	1.1 V	-60	
			f _{in} = 1 MHz (sine wave)	1.4 V	-60	
			(see Figure 9)	1.65 V	-60	
				2.3 V	-60	
				0.8 V	7	
			$C_L = 50 \text{ pF}, R_L = 10 \text{ k}\Omega,$	1.1 V	0.256	
	A or B	B or A	f _{in} = 1 kHz (sine wave)	1.4 V	0.04	
			(see Figure 10)	1.65 V	0.03	
0' " "				2.3 V	0.01	0.4
Sine-wave distortion				0.8 V	3.7	%
			$C_L = 50 \text{ pF}, R_L = 10 \text{ k}\Omega,$	1.1 V	0.4	
	A or B	B or A	f _{in} = 10 kHz (sine wave)	1.4 V	0.04	
			(see Figure 10)	1.65 V	0.02	
				2.3 V	0.02	

Operating Characteristics

T_A = 25°C

	PARAMETER	TEST CONDITIONS	V _{CC} = 0.8 V TYP	V _{CC} = 1.2 V TYP	V _{CC} = 1.5 V TYP	V _{CC} = 1.8 V TYP	V _{CC} = 2.5 V TYP	UNIT
C_{pd}	Power dissipation capacitance	f = 10 MHz	2.5	2.5	2.5	2.5	2.5	pF



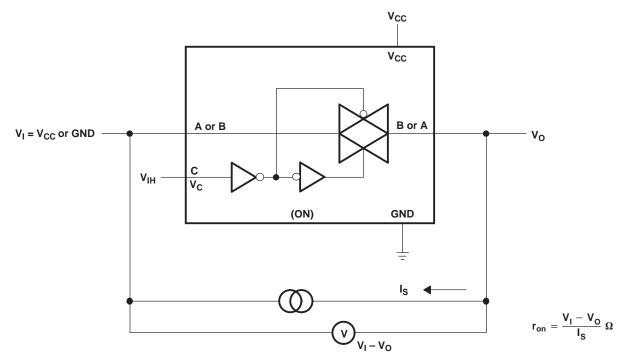


Figure 1. On-State Resistance Test Circuit

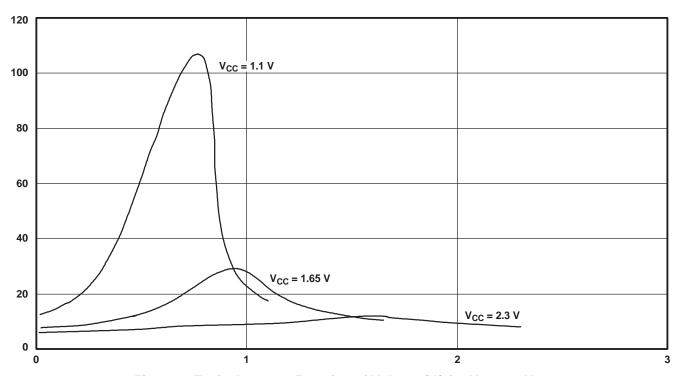


Figure 2. Typical r_{on} as a Function of Voltage (V_I) for $V_I = 0$ to V_{CC}



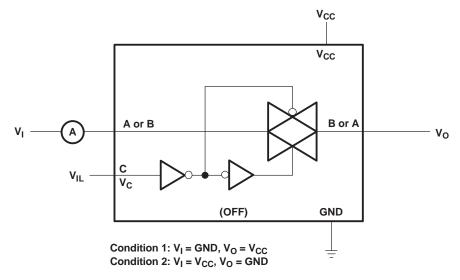


Figure 3. Off-State Switch Leakage-Current Test Circuit

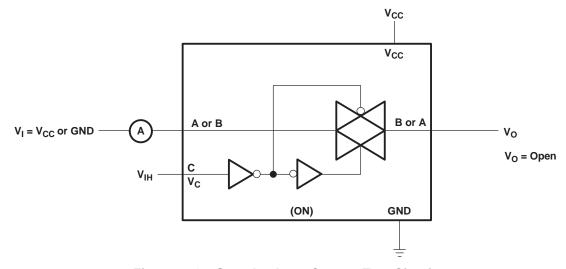
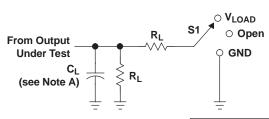


Figure 4. On-State Leakage-Current Test Circuit

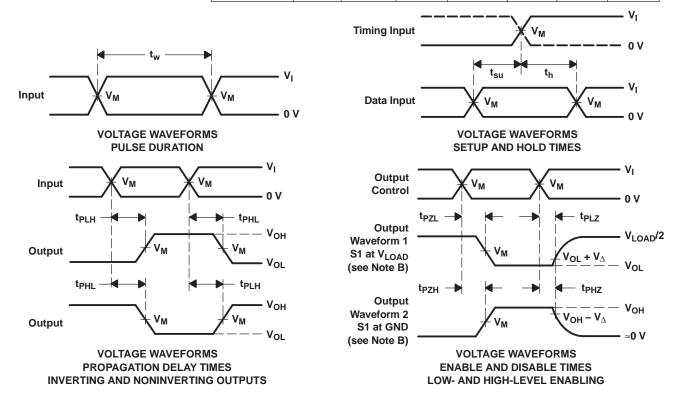




TEST	S1
t _{PLH} /t _{PHL}	Open
t_{PLZ}/t_{PZL}	V _{LOAD}
t _{PHZ} /t _{PZH}	GND

LOAD CIRCUIT

.,	INPUTS		.,	.,		_	.,
V _{CC}	VI	t _r /t _f	V _M	V _{LOAD}	CL	R _L	$V_{\!\scriptscriptstyle \Delta}$
0.8 V	V _{CC}	≤ 2 ns	V _{CC} /2	2×V _{CC}	15 pF	2 k Ω	0.1 V
1.2 V \pm 0.1 V	V _{CC}	≤2 ns	V _{CC} /2	$2 \times V_{CC}$	15 pF	2 k Ω	0.1 V
1.5 V \pm 0.1 V	V _{CC}	≤ 2 ns	V _{CC} /2	2×V _{CC}	15 pF	2 k Ω	0.1 V
1.8 V \pm 0.15 V	V _{CC}	≤ 2 ns	V _{CC} /2	2×V _{CC}	15 pF	2 k Ω	0.15 V
2.5 V \pm 0.2 V	V _{CC}	≤2 ns	V _{CC} /2	2×V _{CC}	15 pF	2 k Ω	0.15 V
1.8 V \pm 0.15 V	V _{CC}	≤2 ns	V _{CC} /2	2×V _{CC}	30 pF	1 k Ω	0.15 V
2.5 V \pm 0.2 V	V _{CC}	≤ 2 ns	V _{CC} /2	$2 \times V_{CC}$	30 pF	500 Ω	0.15 V



- NOTES: A. C_L includes probe and jig capacitance.
 - B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
 - C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_O = 50 Ω , slew rate \geq 1 V/ns.
 - D. The outputs are measured one at a time, with one transition per measurement.
 - E. t_{PLZ} and t_{PHZ} are the same as t_{dis} .
 - F. t_{PZL} and t_{PZH} are the same as t_{en}.
 - G. t_{PLH} and t_{PHL} are the same as t_{pd} .
 - H. All parameters and waveforms are not applicable to all devices.

Figure 5. Load Circuit and Voltage Waveforms



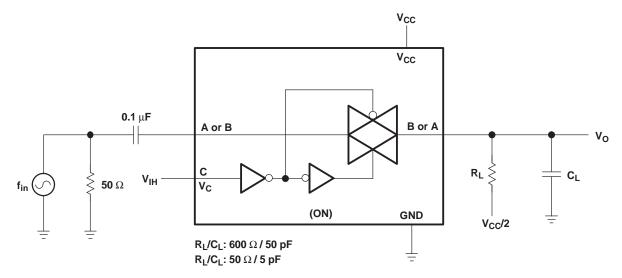


Figure 6. Frequency Response (Switch ON)

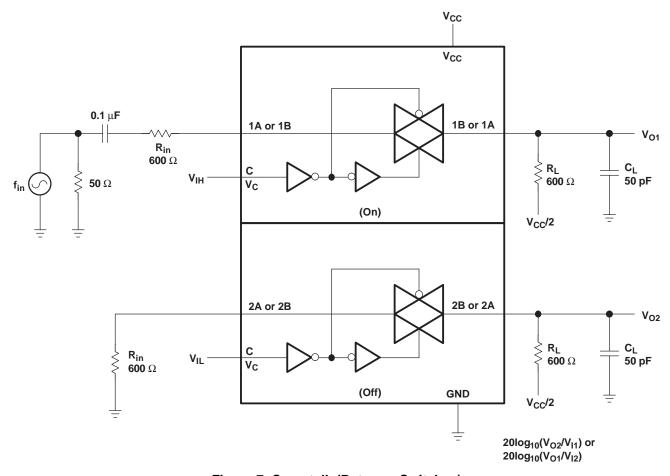


Figure 7. Crosstalk (Between Switches)



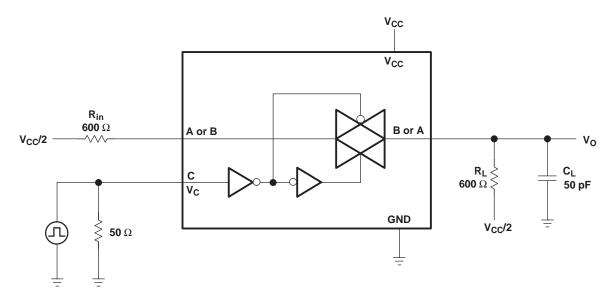


Figure 8. Crosstalk (Control Input - Switch Output)

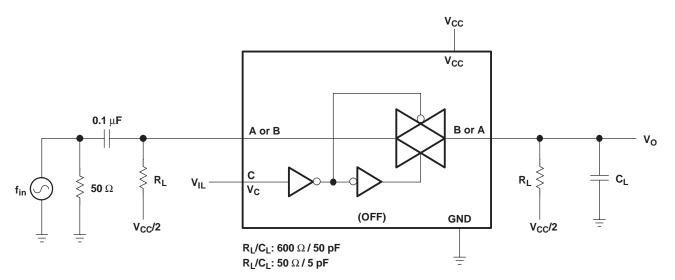


Figure 9. Feedthrough, Switch Off





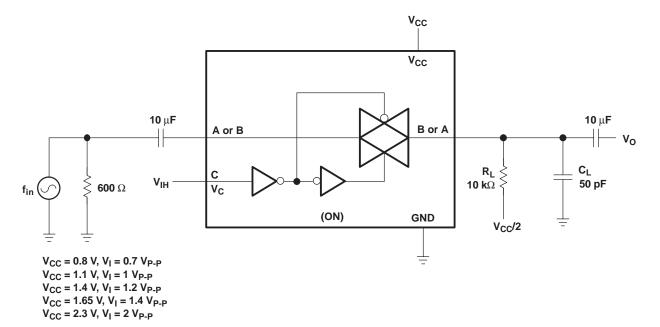


Figure 10. Sine-Wave Distortion

www.ti.com 14-Oct-2022

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
							(6)				
SN74AUC2G66DCTR	ACTIVE	SM8	DCT	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	U66	Samples
										(R, Z)	Samples
SN74AUC2G66DCUR	ACTIVE	VSSOP	DCU	8	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 85	(66, U66Q, U66R)	Samples
										(UR, UZ)	Bampies
SN74AUC2G66DCURG4	ACTIVE	VSSOP	DCU	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	U66R	G 1
											Samples
SN74AUC2G66YZPR	ACTIVE	DSBGA	YZP	8	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	U6N	G
							0				Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE OPTION ADDENDUM

www.ti.com 14-Oct-2022

continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.



www.ti.com 30-May-2024

TAPE AND REEL INFORMATION



TAPE DIMENSIONS KO P1 BO W Cavity A0

A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN74AUC2G66DCTR	SM8	DCT	8	3000	180.0	13.0	3.35	4.5	1.55	4.0	12.0	Q3
SN74AUC2G66DCUR	VSSOP	DCU	8	3000	178.0	9.5	2.25	3.35	1.05	4.0	8.0	Q3
SN74AUC2G66DCUR	VSSOP	DCU	8	3000	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
SN74AUC2G66DCUR	VSSOP	DCU	8	3000	180.0	9.0	2.25	3.4	1.0	4.0	8.0	Q3
SN74AUC2G66DCURG4	VSSOP	DCU	8	3000	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
SN74AUC2G66YZPR	DSBGA	YZP	8	3000	178.0	9.2	1.02	2.02	0.63	4.0	8.0	Q1



www.ti.com 30-May-2024



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
SN74AUC2G66DCTR	SM8	DCT	8	3000	182.0	182.0	20.0
SN74AUC2G66DCUR	VSSOP	DCU	8	3000	202.0	201.0	28.0
SN74AUC2G66DCUR	VSSOP	DCU	8	3000	202.0	201.0	28.0
SN74AUC2G66DCUR	VSSOP	DCU	8	3000	182.0	182.0	20.0
SN74AUC2G66DCURG4	VSSOP	DCU	8	3000	202.0	201.0	28.0
SN74AUC2G66YZPR	DSBGA	YZP	8	3000	220.0	220.0	35.0





NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
 4. Reference JEDEC registration MO-187 variation CA.





NOTES: (continued)

- 5. Publication IPC-7351 may have alternate designs.
- 6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 8. Board assembly site may have different recommendations for stencil design.







NOTES:

- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.





NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.





NOTES: (continued)

- 7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 8. Board assembly site may have different recommendations for stencil design.





DIE SIZE BALL GRID ARRAY



NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.



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